

## GATE CONTROLLED DEVICE - Insulated Gate Bi-polar Transistor - Capsule Type

Old Part Number	PDF Data Sheet Available	New Part Number	V <sub>CES</sub> (V)	V <sub>GES</sub> (V)	I <sub>C</sub> (Note 2) (A)	I <sub>CRM</sub> (Note 2) (A)	I <sub>F</sub> (A)	I <sub>FRM</sub> (A)	P <sub>MAX</sub> (W)	T <sub>J</sub> (Note 3) (°C)	T <sub>stg</sub> (°C)	Rth(j-hs) (IGBT)			Rth(j-hs) (Diode)			Wt (Typ) (g)	Mounting Force (kN)	Outline No. (Note 4)
												Double (K/kW)	Collector (K/kW)	Emitter (K/kW)	Double (K/kW)	Cathode (K/kW)	Anode (K/kW)			
WTC40AAC18	Y	T0400NA18A	1800	+/- 20	400	800	400	800	1800	-60 to +150	-60 to +150	55	90	140	84	138	218	50	8.0 - 12.0	n/a
WTC140AAC18	Y	T1400TA18A	1800	+/- 20	1400	2800	1400	2800	6600	-60 to +150	-60 to +150	15	25	39	35	52	104	120	20.0 - 30.0	n/a

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Note 1 Unless otherwise indicated, T<sub>J</sub> = 125°C

Note 2 T<sub>C</sub> = 90°C

Note 3 For operation below -40°C or above +125°C, please contact the Factory.

Note 4 Please refer to data sheets for outline drawings